



350mA, 20V - 40V Schottky Barrier Diode

FEATURES

- Low forward voltage
- Surface mount device type
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I _F	350	mA	
V_{RRM}	20-40	V	
V _F at I _F =200mA	0.6	V	
T _{J MAX}	125	°C	
Package	SOD-323F		

APPLICATIONS

- Adapters
- For switching power supply
- · Low stored charge
- Inverter

MECHANICAL DATA

- Case: SOD-323F
- Molding compound meets UL 94 V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Polarity: Indicated by cathode band
- Weight: 3.4 mg (approximately)







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	SD103AM3	SD103BM3	SD103CM3	UNIT
Marking code on the device		CA	СВ	CC	
Repetitive peak reverse voltage	V_{RRM}	40	30	20	V
Power dissipation	P _D	200			mW
Forward current	I _F	350			mA
Non-repetitive peak forward surge current @ 8.3ms single half sine wave	I _{FSM}	2			Α
Junction temperature range	T_J	-55 to +125		ç	
Storage temperature range	T _{STG}	-55 to +125			°C

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER		CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Forward voltage (1)		I _F =20mA, T _J =25°C	V_{F}	-	-	0.37	V
		I _F =200mA, T _J =25°C				0.60	
Reverse voltage	SD103AM3			40			
	SD103BM3	I _R =100μA, Τ _J =25°C	V_R	30	-	-	V
	SD103CM3			20			
	SD103AM3	V _R =30V, T _J =25°C					
Reverse current	SD103BM3	V _R =20V, T _J =25°C	I _R	-	-	5	μA
	SD103CM3	V _R =10V, T _J =25°C					
Capacitance		f=1MHz, V _R =0V	С	-	50	-	pF

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION				
ORDERING CODE	PACKAGE	PACKING		
SD103AM3 RRG	SOD-323F	3K / 7" Reel		
SD103BM3 RRG	SOD-323F	3K / 7" Reel		
SD103CM3 RRG	SOD-323F	3K / 7" Reel		



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Typical Forward Characteristics

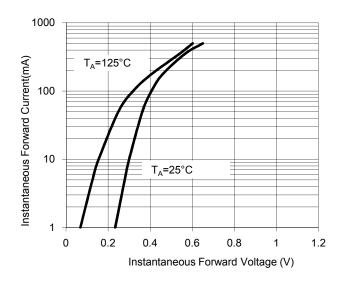


Fig.2 Typical Reverse Characteristics

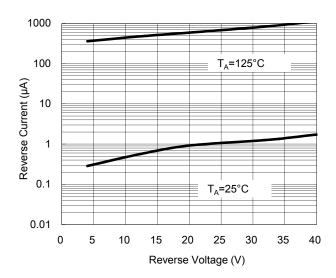


Fig.3 Typical Capacitance Characteristics

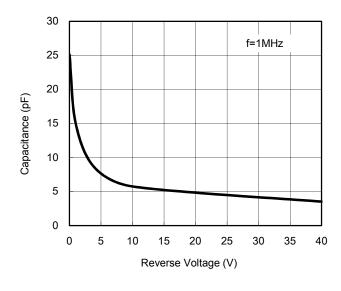
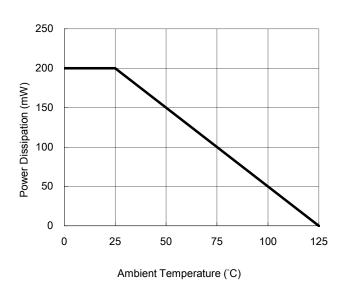


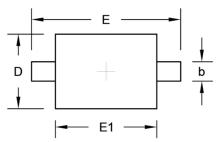
Fig.4 Power Derating Curve

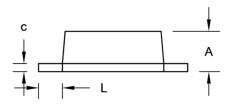




PACKAGE OUTLINE DIMENSION

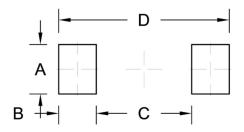
SOD-323F





DIM.	Unit (mm)		Unit (inch)	
DIIVI.	Min.	Max.	Min.	Max.
Α	0.60	0.75	0.024	0.030
b	0.25	0.40	0.010	0.016
С	0.06	0.21	0.002	0.008
D	1.15	1.35	0.045	0.053
Е	2.30	2.70	0.091	0.106
E1	1.60	1.80	0.063	0.071
L	0.30	0.50	0.012	0.020

SUGGEST PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	0.83	0.033
В	0.63	0.025
С	1.60	0.063
D	2.86	0.113



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